

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L10	269465	samsung.as. or lg.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:36
L11	1785231	nec.as. sony.as. hitachi.as. fujifilm.as. sharp.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:28
L12	2053853	10 or 11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:28
L13	27	12 and lcd and (cot near2 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:37
L14	24	13 and (black near2 matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:29
L15	172627	samsung.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:36
L16	1957671	15 or 11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:36
L17	2532454	16 or toshiba.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:37
L18	6	17 and lcd and (cot near2 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:47
L19	535	349/44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:47

L20	275	349/41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:47
L21	1565	349/42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:47
L22	1834	349/43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:47
L23	1546	349/106	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:47
L24	4189	19 20 21 22 23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:48
L25	47	24 and cot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 05:49
L26	40	25 not lg.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 07:41
L27	0	(lcd and cot and (top near2 gate) and (transistor or tft) and source and drain and capacitor and (pixel near2 electrode) and (black near2 matrix) and (color near2 filter)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 07:43
S1	296	349/41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:07
S2	2411	349/42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:07

S3	1732	349/43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:07
S4	2254	349/106	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:07
S5	5669	S1 or S2 or S3 or S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:07
S6	572	S5 and substrate and (tft or (thin near3 film)) and (gate or scan\$4) and (data or signal\$4) and source and drain and (active or semiconductor or amorphous) and (capacitor) and ((black adj matrix) or (light near3 (shield\$4 or block\$4 or absorb\$4))) and (color near3 filter) and pixel and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:17
S7	414	S6 and ((color near4 filter) same (tft or (thin near3 film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:15
S8	237	S6 and ((color near4 filter) near9 (tft or (thin near3 film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:16
S9	467	349/44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:16
S10	54	S8 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:17
S11	53	S10 and insulat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:17

S12	296	349/41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:17
S13	2411	349/42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:17
S14	1732	349/43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:17
S15	2254	349/106	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:17
S16	5669	S12 or S13 or S14 or S15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:17
S17	572	S16 and substrate and (tft or (thin near3 film)) and (gate or scan\$4) and (data or signal\$4) and source and drain and (active or semiconductor or amorphous) and (capacitor) and ((black adj matrix) or (light near3 (shield\$4 or block\$4 or absorb\$4))) and (color near3 filter) and pixel and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:17
S18	237	S17 and ((color near4 filter) near9 (tft or (thin near3 film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:17
S19	467	349/44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:17
S20	54	S18 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:17

S21	53	S20 and insulat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:17
S22	38	S21 and (capacit\$4 near3 storage near3 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 15:33